

TRANSISTOR ARRAY

μ PA2001C, μ PA2002C, μ PA2003C, μ PA2004C

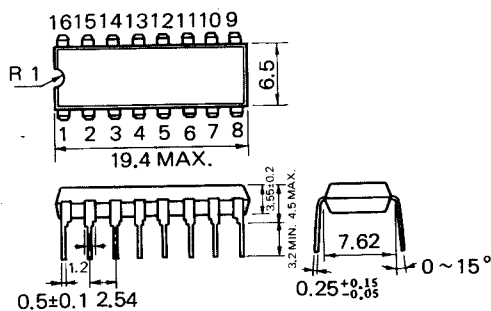
NPN SILICON EPITAXIAL DARLINGTON TRANSISTOR ARRAY

DESCRIPTION

The μ PA2001C, 2002C, 2003C and 2004C are monolithic arrays of seven darlington transistors. These devices are especially suited for driving relays, solenoids, LED, lamps, and other devices with up to 0.3 A output current per unit.

PACKAGE DIMENSIONS

in millimeters



FEATURES

- Transient Protected Outputs
- High DC Current Gain
- High Output Drive Current
- High Output Voltage
- Package is 16 pin PLASTIC DIP

Single Copy
Handle With Care

65

YES

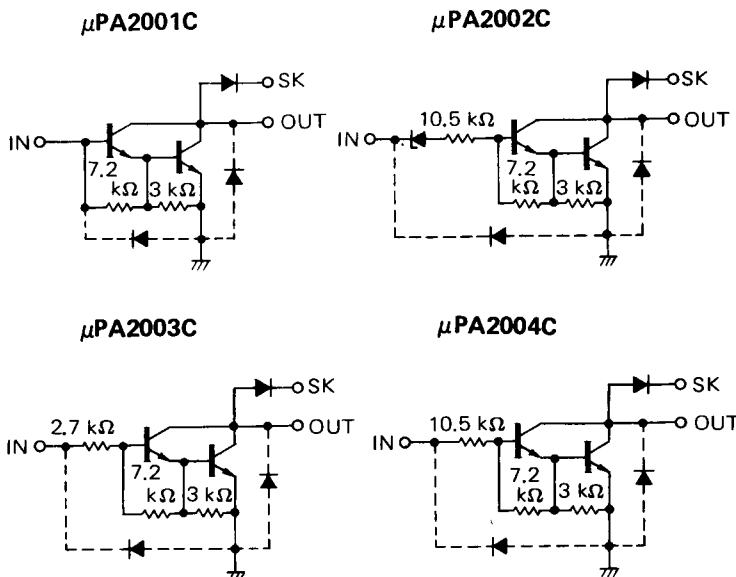
ORIG

003535

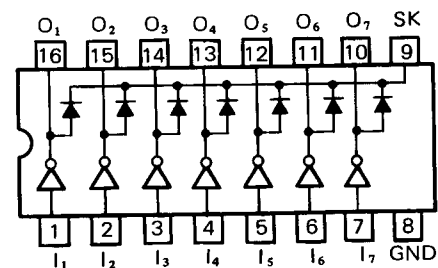
3535

NEC

EQUIVALENT CIRCUIT (1 Unit)



CONNECTION DIAGRAM (Top View)



- I : Input (Base)
- O : Output (Collector)
- GND : (Common Emitter)
- SK : Surge Killer

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

Output Voltage	V_O	60	V
Input Voltage (except $\mu\text{PA2001C}$)	V_I	-0.5 to +30	V
Input Current (only $\mu\text{PA2001C}$)	I_I	25	mA/unit
Output Current	I_O	500	mA/unit
Output Current	I_O^*	2.3	A/package
Reverse Voltage (Clamp Diode)	V_R	60	V
Forward Current (Clamp Diode)	I_F	500	mA/unit

Maximum Power Dissipation

Total Power Dissipation	P_d	900	mW/package
Total Power Dissipation	P_d^*	2.5	W/package

Maximum Temperature

Operating Temperature	T_{opt}	-30 to + 75	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

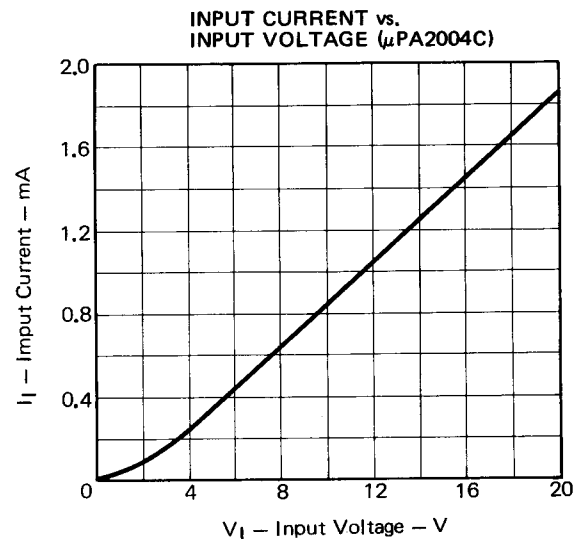
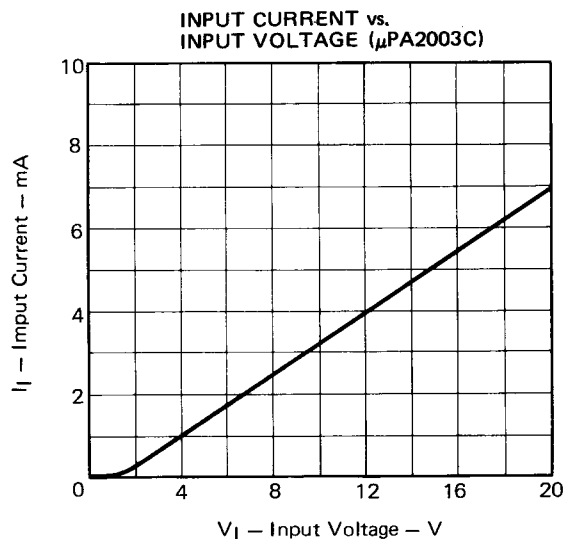
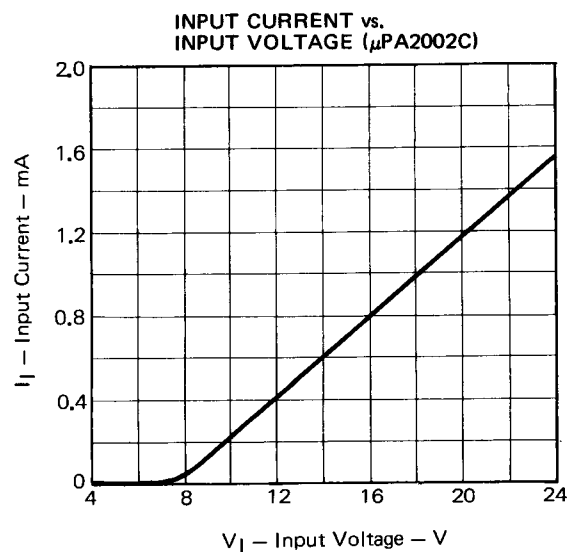
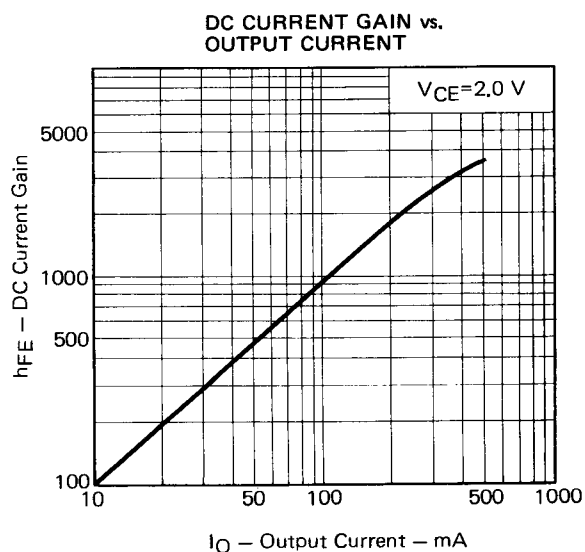
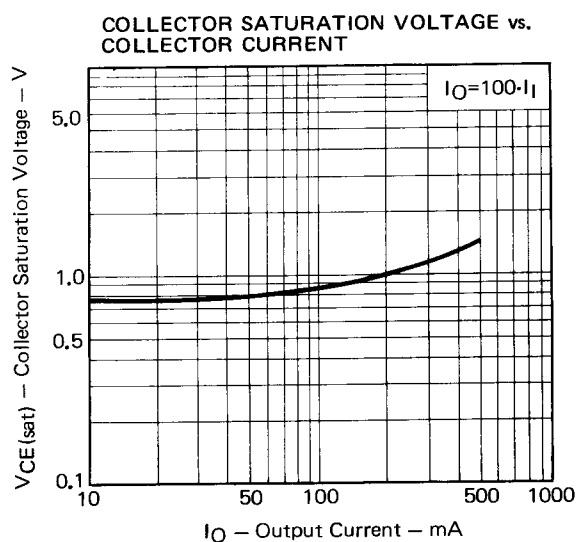
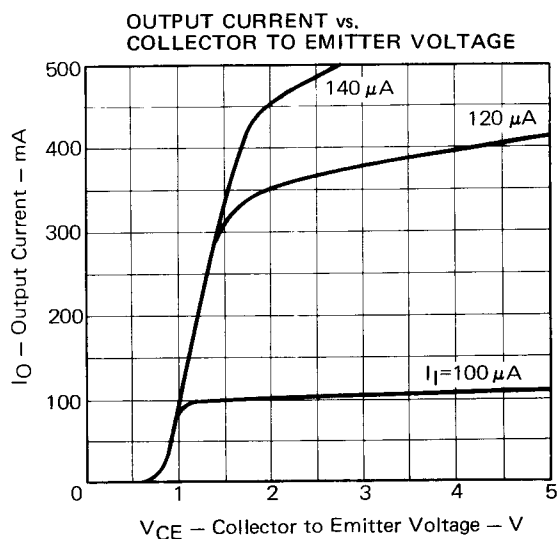
* $PW \leq 20$ ms, duty cycle $\leq 10\%$

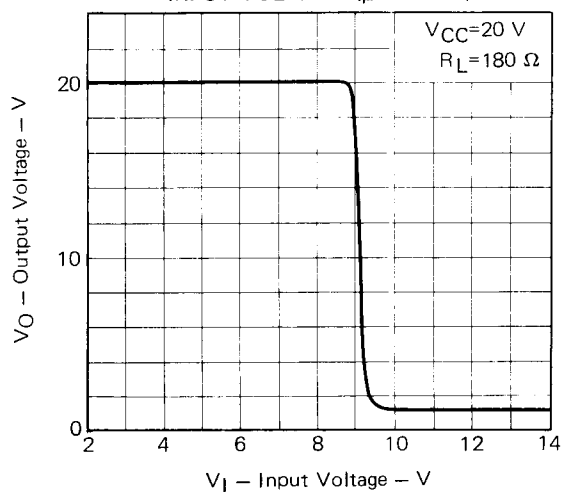
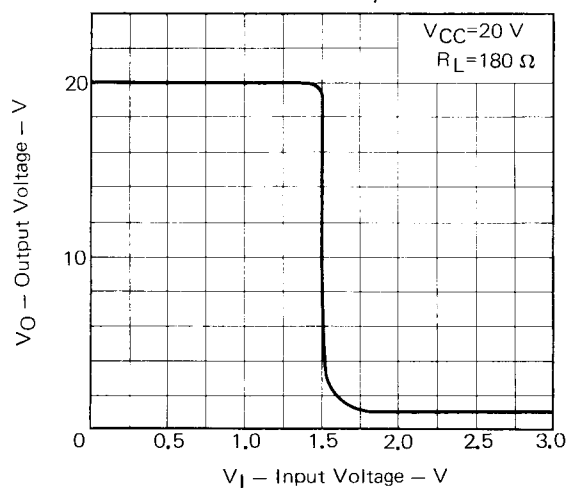
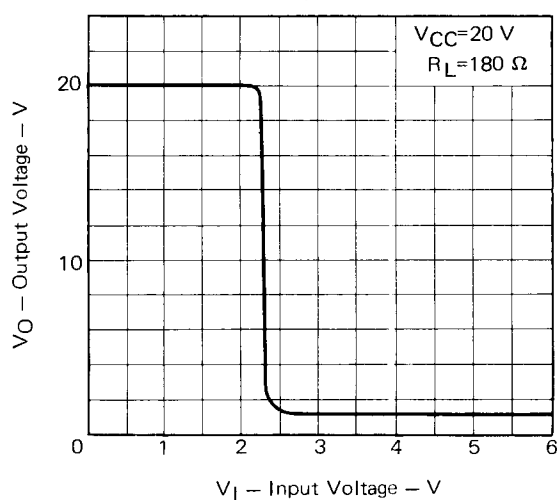
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Output Leakage Current		I_L			10	μA	$V_{CE}=50\text{ V}$
					100	μA	$V_{CE}=50\text{ V}, T_a=70\text{ }^{\circ}\text{C}$
DC Current Gain		h_{FE}	1000	2800			$V_{CE}=2.0\text{ V}, I_O=350\text{ mA}$
Collector Saturation Voltage		$V_{CE(sat)}$		0.9	1.1	V	$I_O=100\text{ mA}, I_I=250\text{ }\mu A$
				1.0	1.3	V	$I_O=200\text{ mA}, I_I=350\text{ }\mu A$
				1.2	1.6	V	$I_O=350\text{ mA}, I_I=500\text{ }\mu A$
Input Voltage	$\mu PA2002C$	V_I			11	V	$V_{CE}=2.0\text{ V}, I_O=100\text{ mA}$
					12	V	$V_{CE}=2.0\text{ V}, I_O=200\text{ mA}$
					13.5	V	$V_{CE}=2.0\text{ V}, I_O=350\text{ mA}$
	$\mu PA2003C$				2.0	V	$V_{CE}=2.0\text{ V}, I_O=100\text{ mA}$
					2.4	V	$V_{CE}=2.0\text{ V}, I_O=200\text{ mA}$
					3.4	V	$V_{CE}=2.0\text{ V}, I_O=350\text{ mA}$
	$\mu PA2004C$				5.0	V	$V_{CE}=2.0\text{ V}, I_O=100\text{ mA}$
					6.0	V	$V_{CE}=2.0\text{ V}, I_O=200\text{ mA}$
					8.0	V	$V_{CE}=2.0\text{ V}, I_O=350\text{ mA}$
Input Current	$\mu PA2002C$	I_I			1.3	mA	$V_I=17\text{ V}$
	$\mu PA2003C$				1.35	mA	$V_I=3.85\text{ V}$
	$\mu PA2004C$				1.0	mA	$V_I=5.0\text{ V}$
Reverse Current (Clamp Diode)		I_R			50	μA	$V_R=50\text{ V}$
Forward Voltage (Clamp Diode)		V_F			2.0	V	$I_F=350\text{ mA}$
Terminal Capacitance		C_t		15		pF	$V_I=0, f=1.0\text{ MHz}$

Note: Input Voltage and Current of the $\mu\text{PA2001C}$ depend on external resistor.

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



OUTPUT VOLTAGE vs.
INPUT VOLTAGE (μ PA2002C)OUTPUT VOLTAGE vs.
INPUT VOLTAGE (μ PA2003C)OUTPUT VOLTAGE vs.
INPUT VOLTAGE (μ PA2004C) **V_O - V_I TEST CIRCUIT**